

NCE N-Channel Super Trench Power MOSFET

Description

The NCEP1545AK uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(on)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

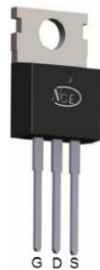
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

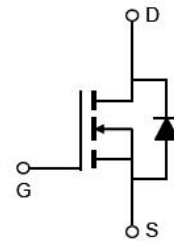
- $V_{DS} = 150V, I_D = 45A$
 $R_{DS(on)} = 22m\Omega$ (typical) @ $V_{GS} = 10V$
 $R_{DS(on)} = 28m\Omega$ (typical) @ $V_{GS} = 4.5V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED!
100% ΔV_{ds} TESTED!

TO-220



Top View



Schematic Diagram

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|-----------|----------------|-----------|------------|----------|
| NCEP1545A | NCEP1545A | TO-220-3L | - | - | - |

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|--------------------|------------|---------------|
| Drain-Source Voltage | V_{DS} | 150 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current-Continuous | I_D | 45 | A |
| Drain Current-Continuous($T_C = 100^\circ C$) | $I_D(100^\circ C)$ | 31.5 | A |
| Pulsed Drain Current | I_{DM} | 180 | A |
| Maximum Power Dissipation | P_D | 120 | W |
| Derating factor | | 0.8 | W/ $^\circ C$ |
| Single pulse avalanche energy (Note 1) | E_{AS} | 100 | mJ |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 175 | $^\circ C$ |

Thermal Characteristic

| | | | |
|--------------------------------------|-----------------|------|--------------|
| Thermal Résistance, Junction-to-Case | $R_{\theta JC}$ | 1.25 | $^\circ C/W$ |
|--------------------------------------|-----------------|------|--------------|

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

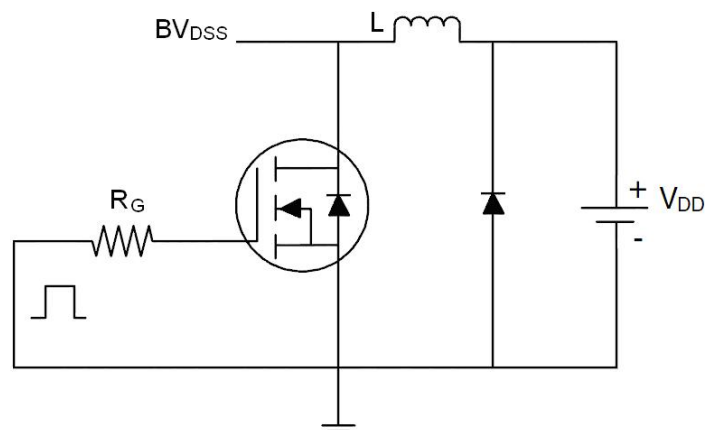
| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|------------------------------------|---------------------|---|-----|------|------|------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =250μA | 150 | - | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =150V,V _{GS} =0V | - | - | 1 | μA |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±20V,V _{DS} =0V | - | - | ±100 | nA |
| On Characteristics | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} ,I _D =250μA | 1.2 | 1.7 | 2.5 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =20A | - | 22 | 27 | mΩ |
| | | V _{GS} =4.5V, I _D =20A | - | 28 | 35 | mΩ |
| Forward Transconductance | g _{FS} | V _{DS} =5V,I _D =20A | 15 | - | - | S |
| Dynamic Characteristics | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} =75V,V _{GS} =0V, F=1.0MHz | - | 1935 | | PF |
| Output Capacitance | C _{oss} | | - | 145 | | PF |
| Reverse Transfer Capacitance | C _{rss} | | - | 11 | | PF |
| Switching Characteristics (Note 2) | | | | | | |
| Turn-on Delay Time | t _{d(on)} | V _{DD} =75V, R _L =7.5Ω V _{GS} =10V,R _G =3Ω | - | 10 | - | nS |
| Turn-on Rise Time | t _r | | - | 6.5 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | | - | 16 | - | nS |
| Turn-Off Fall Time | t _f | | - | 7 | - | nS |
| Total Gate Charge | Q _g | V _{DS} =75V,I _D =20A, V _{GS} =10V | - | 33 | - | nC |
| Gate-Source Charge | Q _{gs} | | - | 7.2 | - | nC |
| Gate-Drain Charge | Q _{gd} | | - | 7.2 | - | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage | V _{SD} | V _{GS} =0V,I _S =20A | - | - | 1.2 | V |
| Diode Forward Current | I _S | | - | - | 45 | A |
| Reverse Recovery Time | t _{rr} | T _J = 25°C, I _F = I _S | - | 30 | - | nS |
| Reverse Recovery Charge | Q _{rr} | di/dt = 100A/μs | - | 135 | - | nC |

Notes:

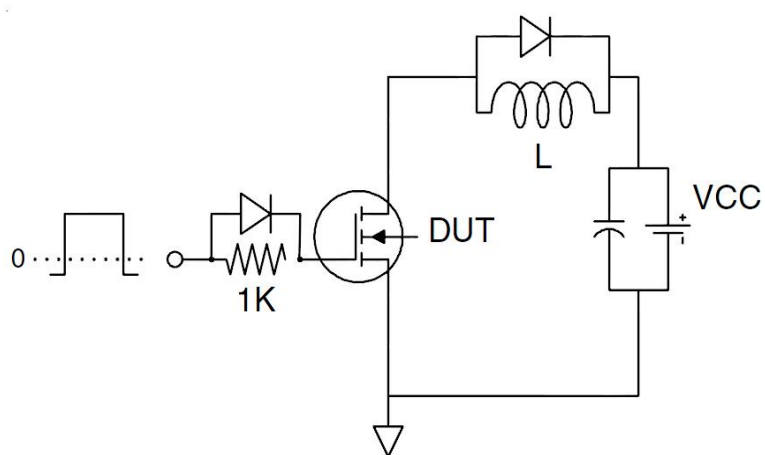
1. EAS condition : $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, L=0.5mH, R_g=25\Omega$
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}=175^{\circ}\text{C}$. The SOA curve provides a single pulse rating.

Test Circuit

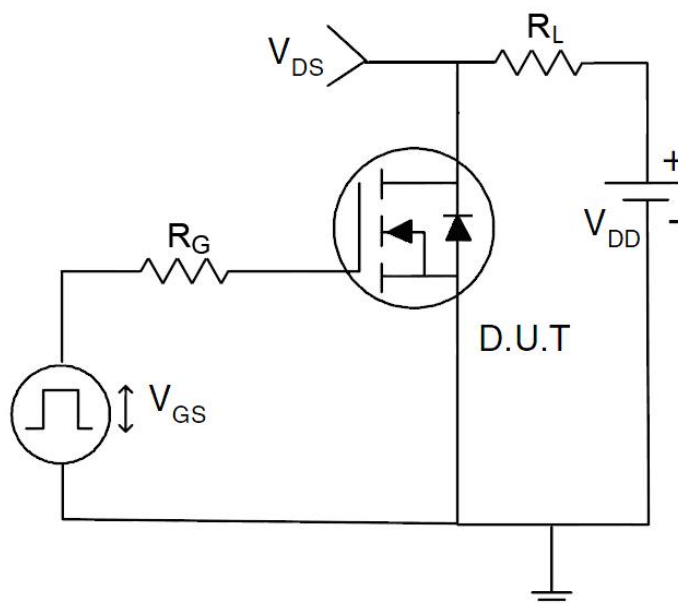
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics

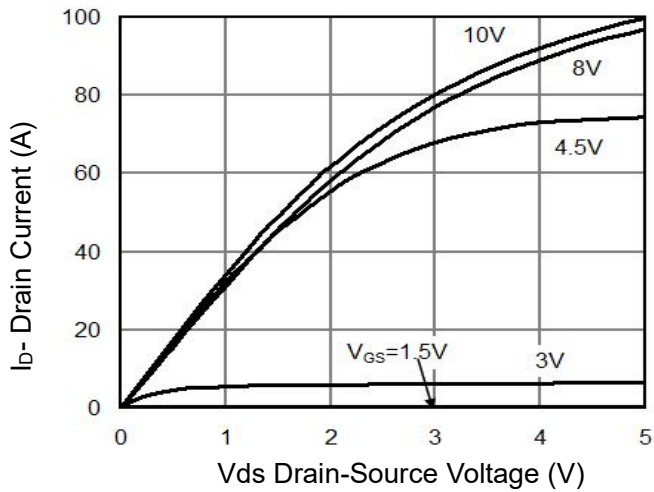


Figure 1 Output Characteristics

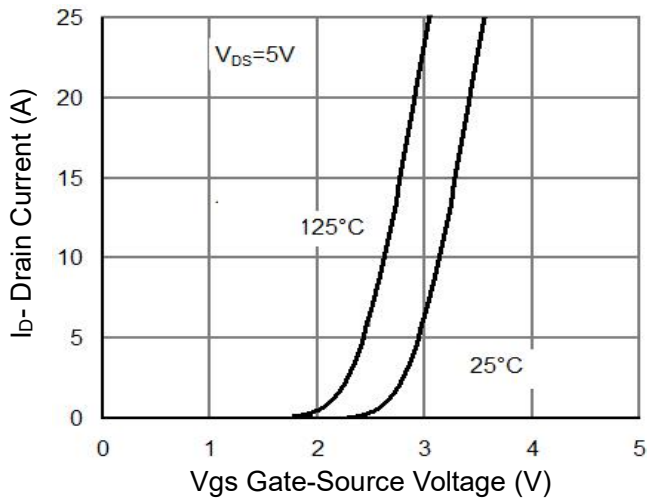


Figure 2 Transfer Characteristics

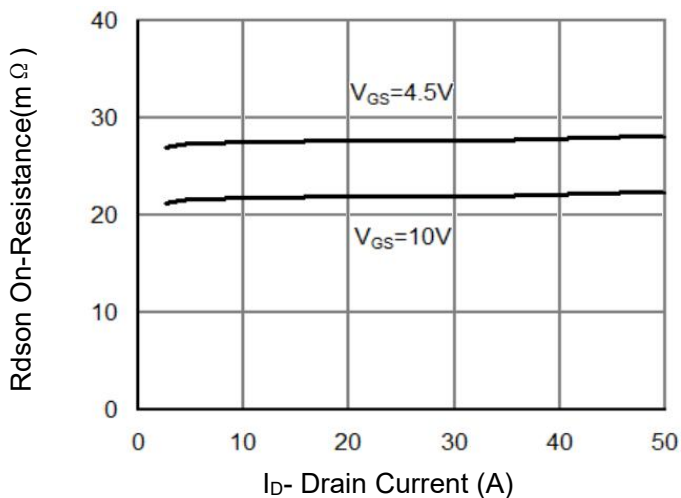


Figure 3 Rdson- Drain Current

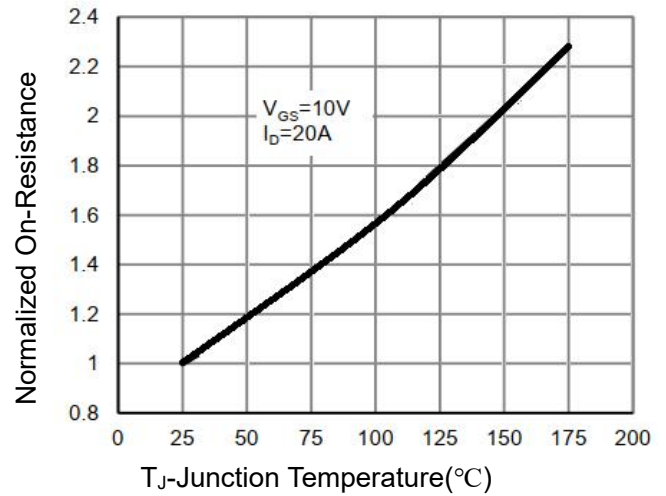


Figure 4 Rdson-Junction Temperature

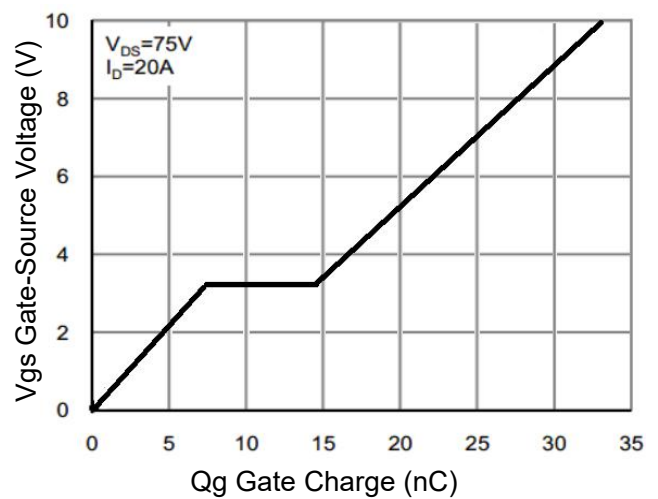


Figure 5 Gate Charge

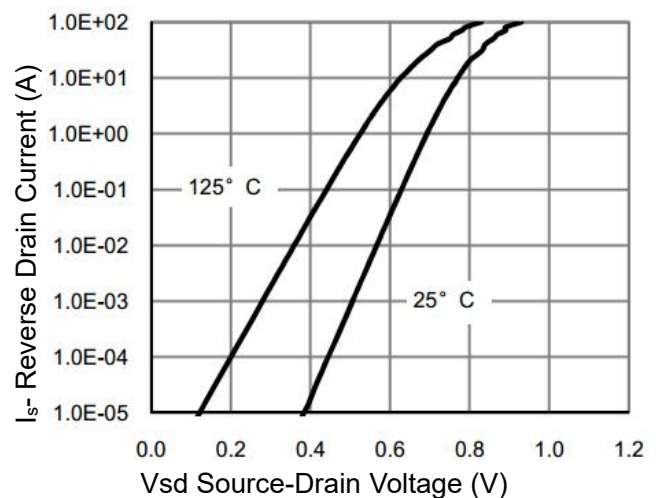


Figure 6 Source- Drain Diode Forward

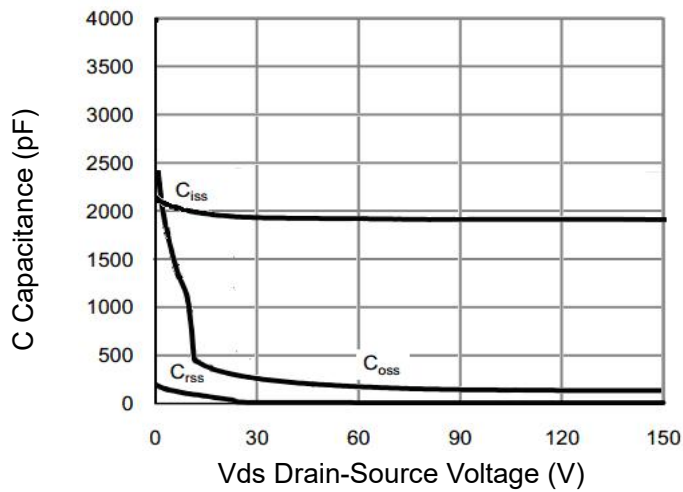


Figure 7 Capacitance vs Vds

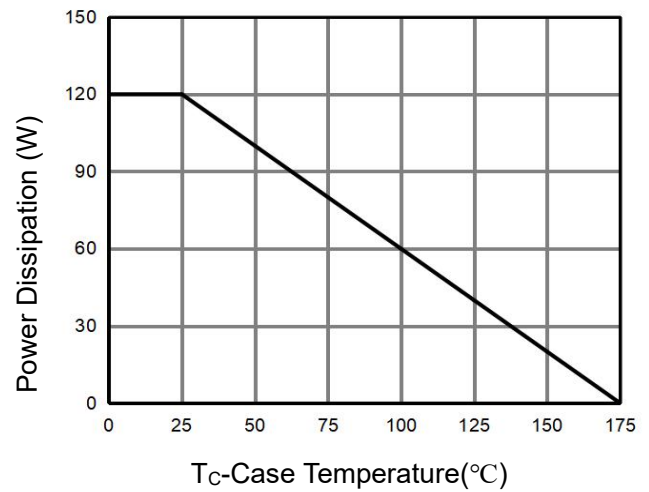


Figure 9 Power De-rating

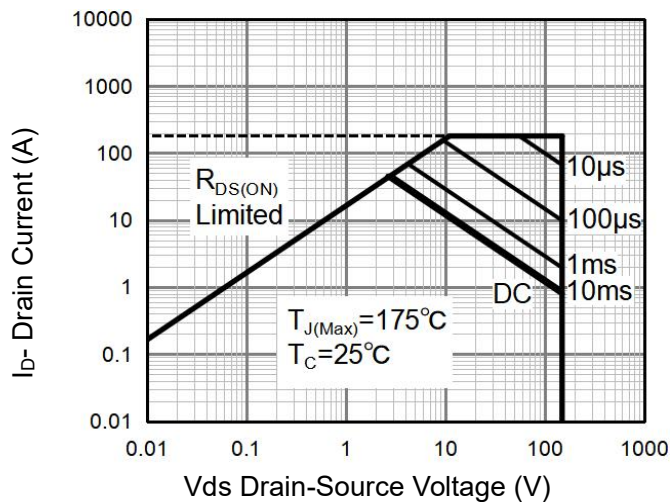


Figure 8 Safe Operation Area (Note3)

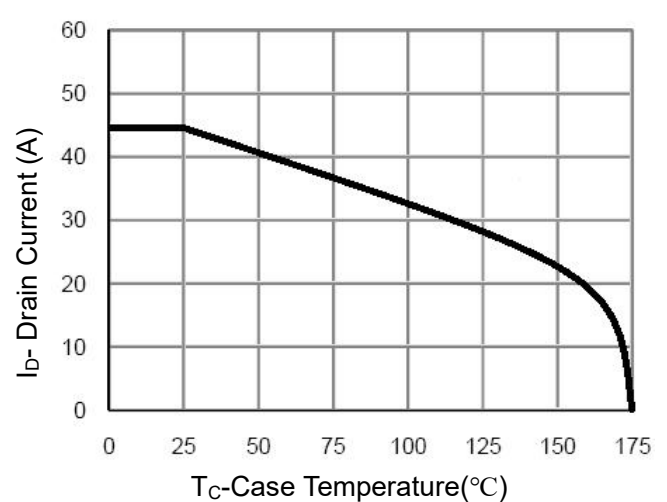


Figure 10 Current De-rating

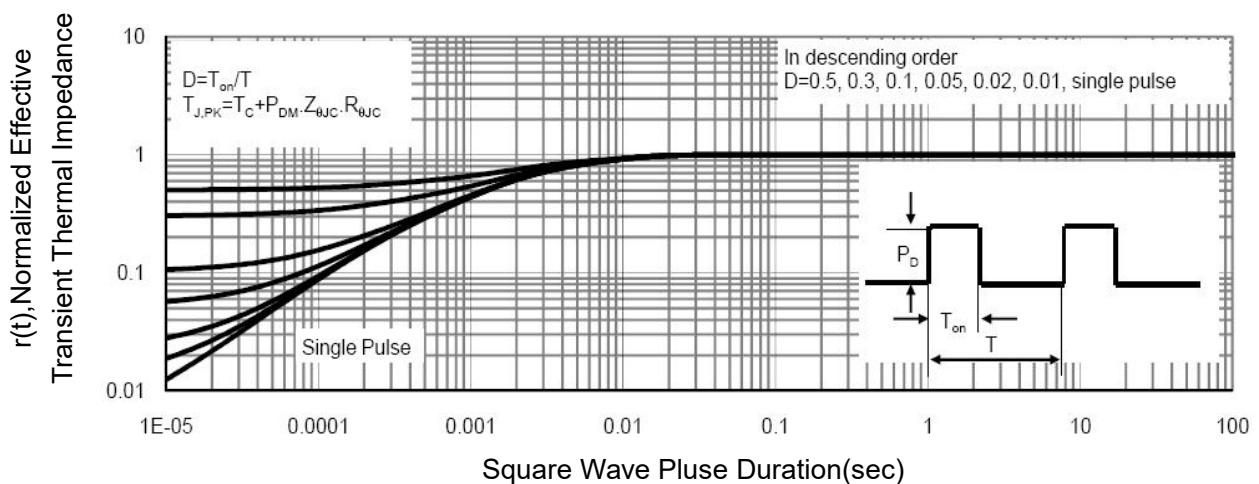
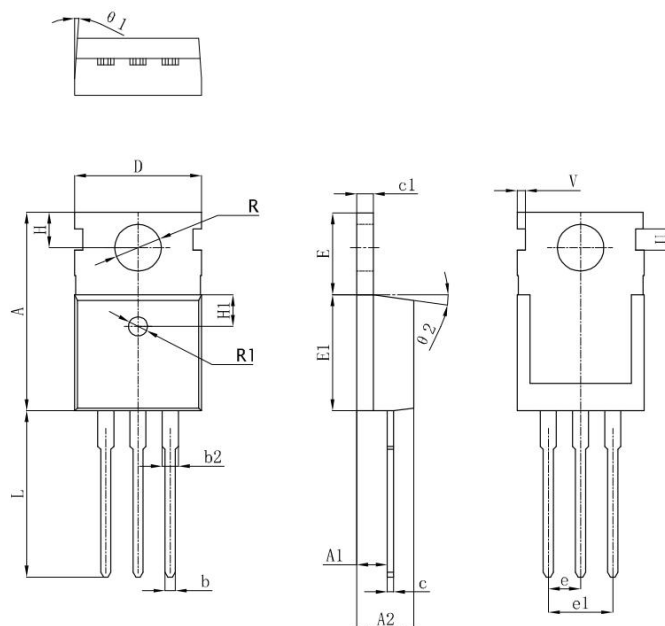


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220-3L Package Information



| SYMBOL | MILLIMETER | | |
|--------|------------|--------|--------|
| | MIN | NOM | MAX |
| A | 15.400 | 15.600 | 15.800 |
| A1 | 2.350 | 2.400 | 2.500 |
| A2 | 4.400 | 4.500 | 4.700 |
| b | 0.700 | 0.800 | 0.900 |
| b2 | 1.180 | 1.310 | 1.440 |
| c | 0.480 | 0.500 | 0.560 |
| c1 | 1.290 | 1.300 | 1.320 |
| D | 9.800 | 10.000 | 10.200 |
| E | 6.400 | 6.500 | 6.600 |
| E1 | 9.000 | 9.100 | 9.200 |
| e | 2.420 | 2.540 | 2.660 |
| e1 | 4.840 | 5.080 | 5.320 |
| H | 2.730 | 2.800 | 2.870 |
| H1 | 2.400 | 2.500 | 2.600 |
| L | 13.020 | 13.370 | 13.720 |
| R | 3.500 | 3.600 | 3.630 |
| R1 | 1.400 | 1.500 | 1.600 |
| U | 1.650 | 1.750 | 1.850 |
| V | 0.580 | 0.680 | 0.780 |
| θ 1 | 2° | 2.5° | 3° |
| θ 2 | 6.5° | 7° | 7.5° |

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